Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1. (amended) An amplifier circuit, comprising:

an amplifier connected between an HF a high frequency (HF) input and an HF output; and

a coupling <u>first</u> circuit connected in parallel to the amplifier between the HF input and the HF output, wherein the coupling <u>first</u> circuit further comprises:

an input bipolar transistor whose having at least one of a collector terminal or and a emitter terminal is high-frequency coupled to the HF input; and

an output diode structure which is high-frequency coupled between the base terminal of the input bipolar transistor and the HF output.

Claim 2. (amended) The amplifier circuit according to claim 1, wherein the amplifier comprises an amplifier bipolar transistor whose having a base terminal is high-frequency coupled to the HF input, wherein the input bipolar transistor of the eoupling first circuit is operably connected in order to draw the base potential of the amplifier bipolar transistor to such a potential that the amplifier is switched off when the eoupling first circuit is switched on.

Claim 3. (amended) The amplifier circuit according to claim 1, wherein at least one of the emitter terminal of and the collector terminal of the input bipolar transistor of the coupling circuit, which is nothigh-frequency coupled to the HF input, is connected to ground via a resistor.

Claim 4. (amended) The amplifier circuit according to claim 1, wherein the eoupling first circuit further comprises a bias input coupled to receive a bias voltage and further coupled to apply the a circuit for applying a bias voltage to the input coupling bipolar transistor and the diode structure in order to thereby switch on the eoupling first circuit.

Claim 5. (amended) The amplifier circuit according to claim 4, wherein the collector terminal of the eoupling input bipolar transistor is high-frequency coupled to the HF input, wherein the eircuit for applying a bias voltage is implemented to operate the collector base diode of the input-bipolar transistor and the diode structure in saturation in flow direction when the eoupling first circuit is switched on and to operate the collector base diode of the input bipolar transistor and the diode structure in reverse direction when the eoupling first circuit is switched off.

Claim 6. (amended) The amplifier circuit according to claim 4, wherein the circuit for applying the bias voltage applies the bias voltage depending depends on a level of the HF input signal.

Claim 7. (amended) The amplifier circuit according to claim 1, wherein the output diode structure comprises is at least one of the base collector diode of and the base emitter diode of an output a bipolar transistor.

Claim 8. (amended) The amplifier circuit according to claim 7, wherein the collector terminal of the output bipolar transistor is connected to the base terminal of the output bipolar transistor, wherein the base terminals of the input bipolar transistor and the output bipolar transistor are connected via a resistor to the bias input terminal, and wherein a resistor is connected between the HF output and the emitter terminal of the output bipolar transistor.

Claim 9. (amended) The amplifier circuit according to claim 7, wherein the collector terminal of the output bipolar transistor is connected to the HF output and wherein the emitter terminal of the output bipolar transistor is connected to ground via a resistor.

Claim 10. (amended) The amplifier circuit according to claim 9, further comprising a wherein the circuit for applying the a supply voltage, the circuit for applying the supply voltage including comprise a bias circuit bipolar transistor, whose having a collector terminal and a base terminal that are connected to each other and via a resistor to a bias terminal, wherein the whose emitter terminal of the bias circuit bipolar transistor is connected to ground via a resistor, and whose the base terminal of the bias circuit bipolar

<u>transistor</u> is connected to the base terminal of the input bipolar transistor and connected to the base terminal of the <u>output</u> bipolar transistor.

Claim 11. (new) An amplifier circuit, comprising:

an amplifier connected between an input and an output; and

a first circuit connected in parallel to the amplifier between the input and the output, wherein the first circuit further comprises:

a first bipolar transistor having at least one of a collector terminal and an emitter terminal coupled to the input; and

a second bipolar transistor having a base coupled to a base of the first bipolar transistor, the second bipolar transistor having one of a collector terminal and an emitter terminal coupled directly to the base, and the other of the collector terminal and the emitter terminal coupled to the output.

Claim 12. (new) The amplifier circuit of claim 11, wherein the amplifier comprises an amplifier bipolar transistor having a base terminal coupled to the input, wherein the input bipolar transistor of the first circuit is operably connected to draw the base potential of the amplifier bipolar transistor to such a potential that the amplifier is switched off when the first circuit is switched on.

Claim 13. (amended) The amplifier circuit according to claim 11, wherein at least one of the emitter terminal and the collector terminal of the input bipolar transistor is connected to ground via a resistor.

Claim 14. (new) The amplifier circuit of claim 15, further comprising a resistor coupled between the emitter terminal of the second bipolar transistor and the output.

Claim 15. (new) An amplifier circuit, comprising:

an amplifier connected between an input and an output; and

a first circuit connected in parallel to the amplifier between the input and the output, wherein the first circuit further comprises:

a first bipolar transistor having at least one of a collector terminal and an emitter terminal coupled to the input;

a second bipolar transistor having a base coupled to a base of the first bipolar transistor, the second bipolar transistor having one of a collector terminal and an emitter terminal coupled directly to the base of the second bipolar transistor; and

a diode structure coupled between the base of the first bipolar transistor and the output.

Claim 16. (new) The amplifier circuit of claim 15, wherein the diode structure is a base emitter junction of the second bipolar transistor.

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Claim 17. (new) The amplifier circuit of claim 15, wherein the diode structure is a

collector base junction of a third bipolar transistor.

Claim 18. (new) The amplifier circuit of claim 17, wherein the third bipolar transistor

includes a base connected to the base of the first transistor.

Claim 19. (new) The amplifier circuit of claim 15, wherein the amplifier comprises an

amplifier bipolar transistor having a base terminal coupled to the input, wherein the input

bipolar transistor of the first circuit is operably connected to draw the base potential of

the amplifier bipolar transistor to such a potential that the amplifier is switched off when

the first circuit is switched on.

Claim 20. (amended) The amplifier circuit according to claim 15, wherein at least one of

the emitter terminal and the collector terminal of the input bipolar transistor is connected

to ground via a resistor.

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